

isc Silicon PNP Power Transistor

KTA1700

**DESCRIPTION**

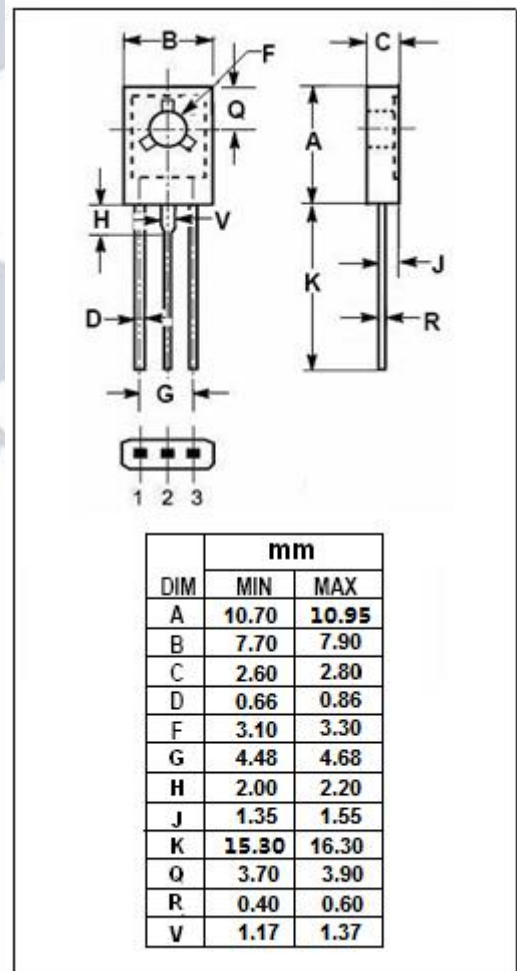
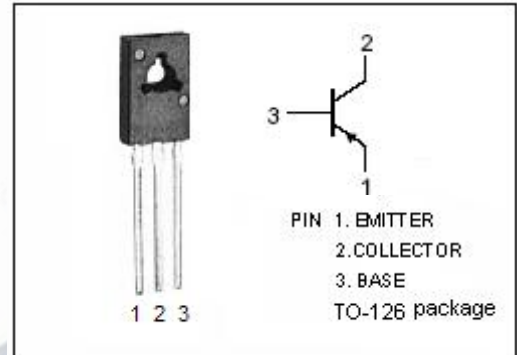
- High Collector-Emitter Breakdown Voltage  
 $V_{CEO} = -160V(\text{Min})$
- Complement to Type KTC2800

**APPLICATIONS**

- Designed for high voltage applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-160	V
$V_{CEO}$	Collector-Emitter Voltage	-160	V
$V_{EBO}$	Emitter-Base Voltage	-5.0	V
$I_{C(DC)}$	Collector Current(DC)	-1.5	A
$I_{B(DC)}$	Base Current	-1.0	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	10	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



**isc Silicon PNP Power Transistor****KTA1700****ELECTRICAL CHARACTERISTICS**T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = 0	-160			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -500mA; I <sub>B</sub> = -50mA			-1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -500mA; V <sub>CE</sub> = -5V			-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -160V; I <sub>E</sub> = 0			-1.0	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-1.0	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -100mA; V <sub>CE</sub> = -5V	70		240	
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V; f= 1.0MHz		30		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> =-100mA; V <sub>CE</sub> = -10V		100		MHz

◆ **h<sub>FE</sub> Classifications**

O	Y
70-140	120-240